



FEATURES

- Ideal for electron detection
- Large detection area
- 100% internal QE

Dimensions are in inch [metric] units.

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area	10mm x 10mm		100		mm ²
Responsivity, \mathcal{R}	@ 254nm, $V_R = 0V$	0.07	0.08	0.09	A/W
Shunt Resistance, R_{sh}	$V_B = \pm 10mV$	20			M-ohm
Reverse Breakdown Voltage, V_R	$I_R = 1\mu A$		10		Volts
Capacitance, C	$V_R = 0V$		10	44	nF
Rise Time	$V_R = 0V, R_L = 50\Omega$			10	usec

THERMAL PARAMETERS

STORAGE AND OPERATING TEMPERATURE RANGE	
Ambient ²	-10° TO 40°C ²
Nitrogen or Vacuum	-20°C TO 80°C
Maximum Junction Temperature	70°C
Lead Soldering Temperature ¹	260°C

¹0.08" from case for 10 seconds.

²Temperature exceeding these parameters may create Oxide growth on the active area. Over time Responsivity to Low energy radiation and wavelengths below 150nm will Be Compromised.

Shipped with temporary cover to protect photodiode and wire bond. Review Opto Diode "Handling Precautions for IRD Detectors" prior to removing cover.

